

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of  
Ryoji HOSHI et al.

0112 Rec'd PCT/PTO 0 4 JAN 2005

Application No.: New U.S. National Stage of PCT/JP03/08671

Filed: January 4, 2005

Docket No.: 122336

For: A SILICON WAFER FOR EPITAXIAL GROWTH, AN EPITAXIAL WAFER, AND A  
METHOD FOR PRODUCING IT

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of references 2-4 is discussed in the present specification.
- ☒ 3. References 1, 5-6, 8-9 were cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information.
- ☒ 4. In accordance with 37 CFR §1.98(a)(2)(i), copies of any U.S. patents and patent application publications are not attached.
- ☒ 5. English language Abstracts of non-English language references 2-9 are attached hereto.
- ☒ 6. Computer-generated English language translation of the following Japanese references have been obtained from the website of the Japanese Patent Office ([<http://www.jpo.go.jp>]), and are attached, but have not been reviewed for accuracy. See References 2-4, 6-9.
- ☒ 7. Reference 7 corresponds to Reference 1. Reference 3 corresponds to WO 01/38611 A1, which is cited in the International Search Report.

Respectfully submitted,

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WPB:EDM/nxy

Date: January 4, 2005

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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 122336		APPLICATION NO. New U.S. National Stage of PCT/JP03/08671	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Ryoji HOSHI et al.			
				FILING DATE January 4, 2005			

  

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
	1.	US 2002/0000189 A1	01/03/2002	Tadami TANAKA et al.		

  

FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
	2.	JP-A-2000-044389 w/ abst. & trans.	02/15/2000	JAPAN		
	3.	JP-A-2001-151596 w/ abst. & trans.	06/05/2001	JAPAN		
	4.	JP-A-2000-219598 w/ abst. & trans.	08/08/2000	JAPAN		
	5.	WO 01/27362 A1 w/ abst.	04/19/2001	JAPAN		
	6.	JP-A-2001-274167 w/ abst. & trans.	10/05/2001	JAPAN		
	7.	JP-A-2002-012499 w/ abst. & trans.	01/15/2002	JAPAN		
	8.	JP-A-2000-109396 w/ abst. & trans.	04/18/2000	JAPAN		
	9.	JP-A-2002-076007 w/ abst. & trans.	03/15/2002	JAPAN		

  

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
	10.	Talid SINNO et al.; "Modeling Microdefect Formation in Czochralski Silicon"; <i>Journal of the Electrochemical Society</i> ; 146 (6); 1999; pp. 2300-2312.

  

EXAMINER	DATE CONSIDERED
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Date: January 4, 2005